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DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	$24m\Omega$ @ $V_{GS} = 4.5V$	8A
20V	29mΩ @ V _{GS} = 2.5V	5.5A
	37mΩ @ V _{GS} = 1.8V	4.8A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- _

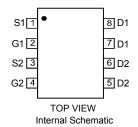
Features

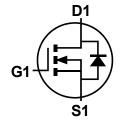
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

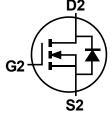
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.072g (approximate)









N-Channel MOSFET

N-Channel MOSFET

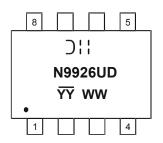
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG9926USD-13	SO-8	2.500/Tape & Reel

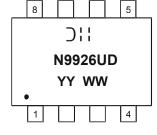
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

O|| = Manufacturer's Marking
N9926UD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)

 $\frac{YY}{YY}$ = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\frac{YY}{YY}$ = Date Code Marking for CAT (Chengdu Assembly/ Test site)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	20	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	I _D	8 6.7	А
Pulsed Drain Current (Note 6)			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.3	W
Thermal Resistance, Junction to Ambient	R _{0JA}	96	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

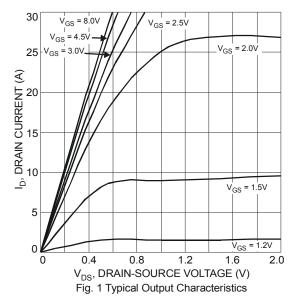
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

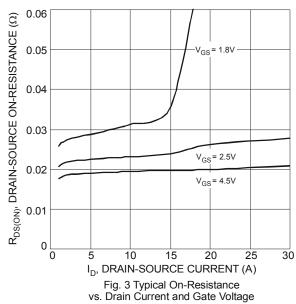
Characteristic	Cumbal	Min	Tura	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition	
	D) /	20	I		١,,	N/ 01/1 050::A	
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5		0.9	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			19 23	-		$V_{GS} = 4.5V, I_D = 8.2A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_			mΩ	$V_{GS} = 2.5V, I_D = 3.3A$	
			29	37		$V_{GS} = 1.8V, I_D = 2A$	
Forward Transfer Admittance	Y _{fs}	_	7	_	S	$V_{DS} = 10V, I_{D} = 4A$	
Diode Forward Voltage		0.5	_	0.9	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						_	
Input Capacitance	C _{iss}	_	867	_	pF	V _{DS} = 15V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	85	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	81	_	pF		
Gate Resistance	Rg	_	1.29	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	Q_g	_	8.8	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 8.2A	
Gate-Source Charge	Q_{gs}	_	1.2	_	nC		
Gate-Drain Charge	Q_{gd}	_	3	_	nC		
Turn-On Delay Time	t _{d(on)}	_	13.2	_	ns		
Turn-On Rise Time	t _r	_	12.6	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{d(off)}	_	64.8	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	_	21.7	_	ns		

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by function temperature.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







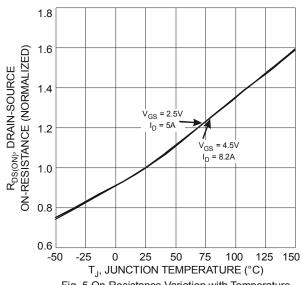
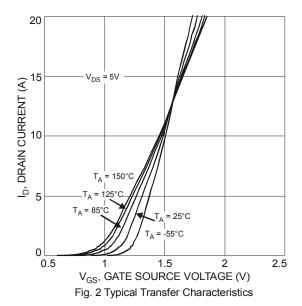


Fig. 5 On-Resistance Variation with Temperature



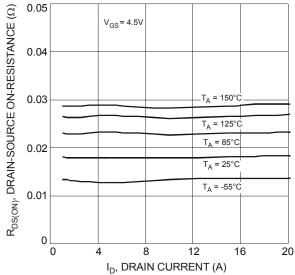


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

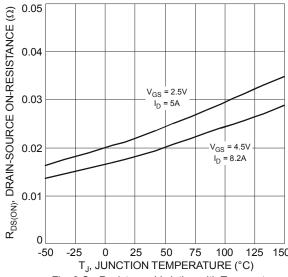


Fig. 6 On-Resistance Variation with Temperature

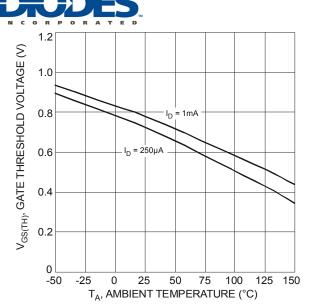
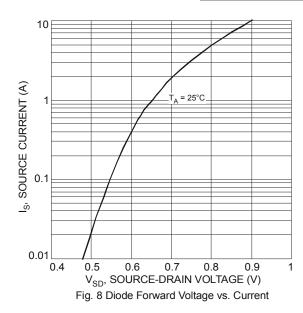
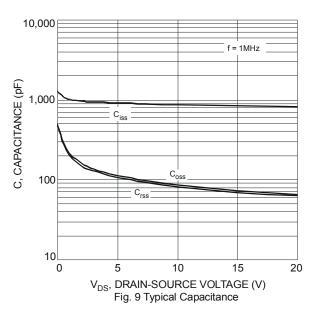


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





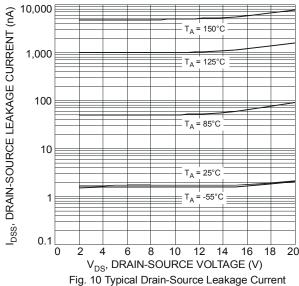


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

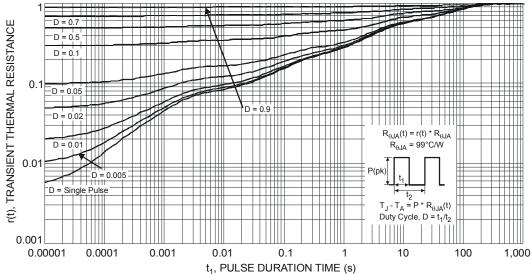
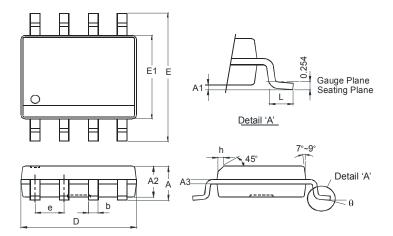


Fig. 11 Transient Thermal Response



Package Outline Dimensions

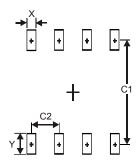
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOP-8L				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27	Тур		
h	-	0.35		
٦	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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